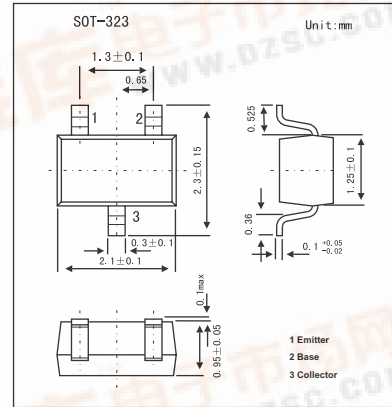


SMD Type Transistors

NPN Epitaxial Planar Silicon Transistor
2SC4555

■ Features

- Very small-sized package
- Low collector-to-emitter saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	20	V
Collector-emitter voltage	V _{CEO}	15	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	500	mA
Collector current(Pulse)	I _{CP}	1	A
Collector dissipation	P _C	150	mW
Junction temperature	T _j	105	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CB0}	V _{CB} = 15V, I _E =0			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 4V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} = 2V, I _C = 10mA	135		600	
Gain bandwidth product	f _T	V _{CE} = 2V, I _C = 50mA		300		MHz
Output capacitance	C _{ob}	V _{CB} = 10V, f = 1MHz		4.0		pF
Collector-to-emitter saturation voltage	V _{CE(sat)}	I _C = 5mA, I _B = 0.5mA			30	V
		I _C = 200mA, I _B = 10mA		160	300	
Base-to-emitter saturation voltage	V _{BE(sat)}	I _C = 200mA, I _B = 10mA		0.95	1.2	V
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	20			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	15			V
Emitter-to-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5			V

■ hFE Classification

Marking	UT		
	5	6	7
Rank	135~270	200~400	300~600



